

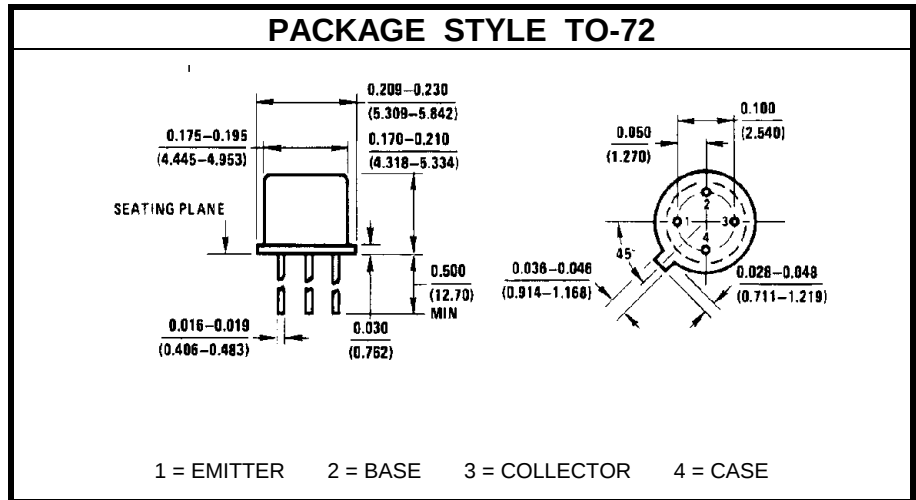
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **ASI MM8006** is Designed for High Frequency Low Noise Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	50 mA
V_{CBO}	15 V
P_{DISS}	600 mW @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+200^\circ C$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 3.0 mA			10			V
BV_{CBO}	I _C = 1.0 μA			15			V
I_{CBO}	V _{CB} = 15 V V _{CB} = 15 V	T _A = 150 °C				0.01 1.0	μA
BV_{EBO}	I _E = 10 μA			3.0			V
h_{FE}	V _{CE} = 1.0 V	I _C = 1.0 mA		25			---
V_{CE(SAT)}	I _C = 10 mA	I _B = 1.0 mA				0.4	V
V_{BE(SAT)}	I _C = 10 mA	I _B = 1.0 mA				1.0	V
f_t	V _{CE} = 10 V	I _C = 4.0 mA	f = 100 MHz	1000			MHz
C_{ob}	V _{CB} = 0 V	f = 140 KHz				3.0	pF
	V _{CB} = 10 V	f = 140 KHz				1.7	
C_{ib}	V _{EB} = 0.5 V	f = 140 KHz				2.0	pF
N_F	V _{CE} = 6.0 V	I _C = 1.0 mA	f = 60 MHz			6.0	dB
G_{pe}	V _{CB} = 12 V	I _C = 6.0 mA	f = 200 MHz	15			dB
P_{out} η	V _{CB} = 15 V	I _C = 8.0 mA	f = 500 MHz	30			mW %
				25			